

Fig.1

Inventor: Donghang YAN et al.  
Title: Heterojunction Organic Semiconductor Field  
Effect Transistor (FET) with a Gate Insulation  
Layer and Manufacturing Process Thereof  
Attorney Docket No.: 33419-190319

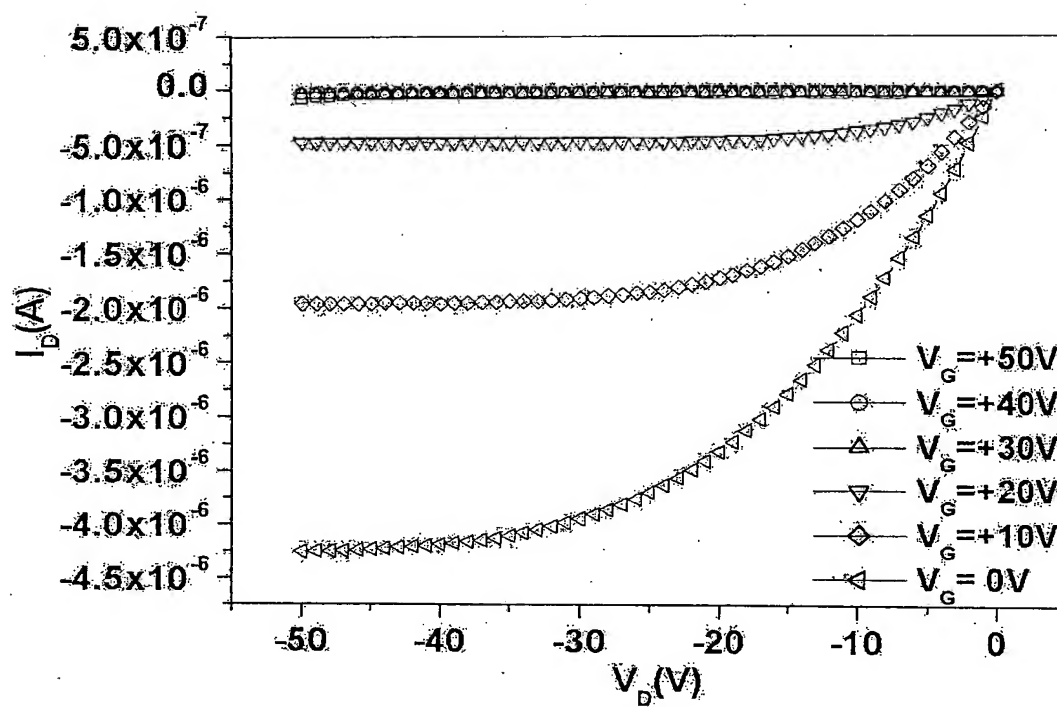


Fig.2

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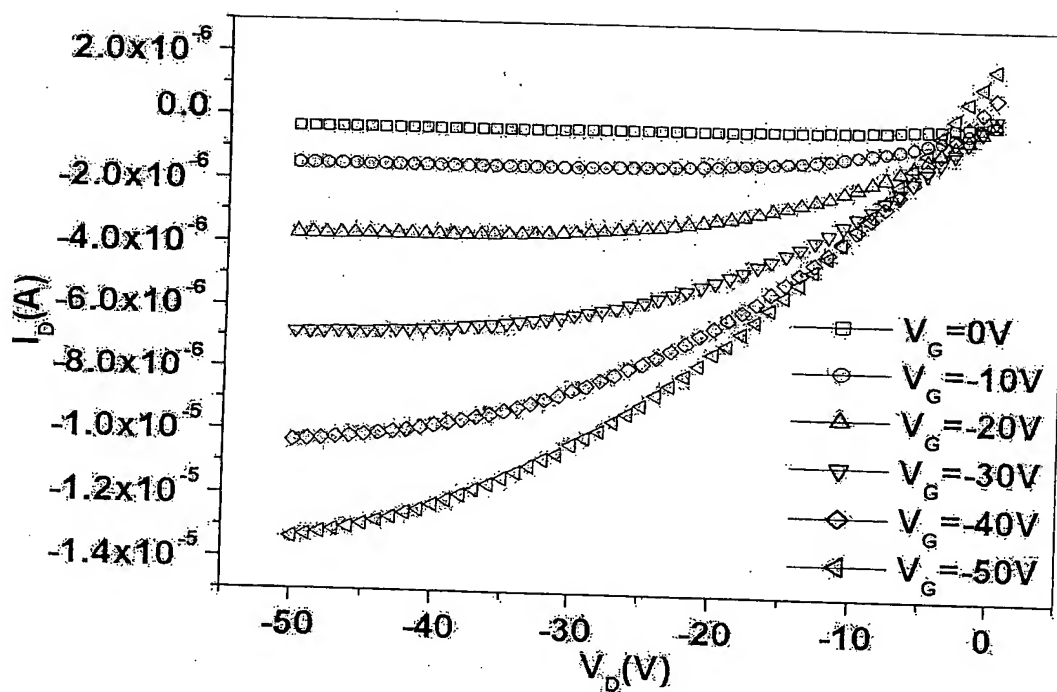


Fig.3

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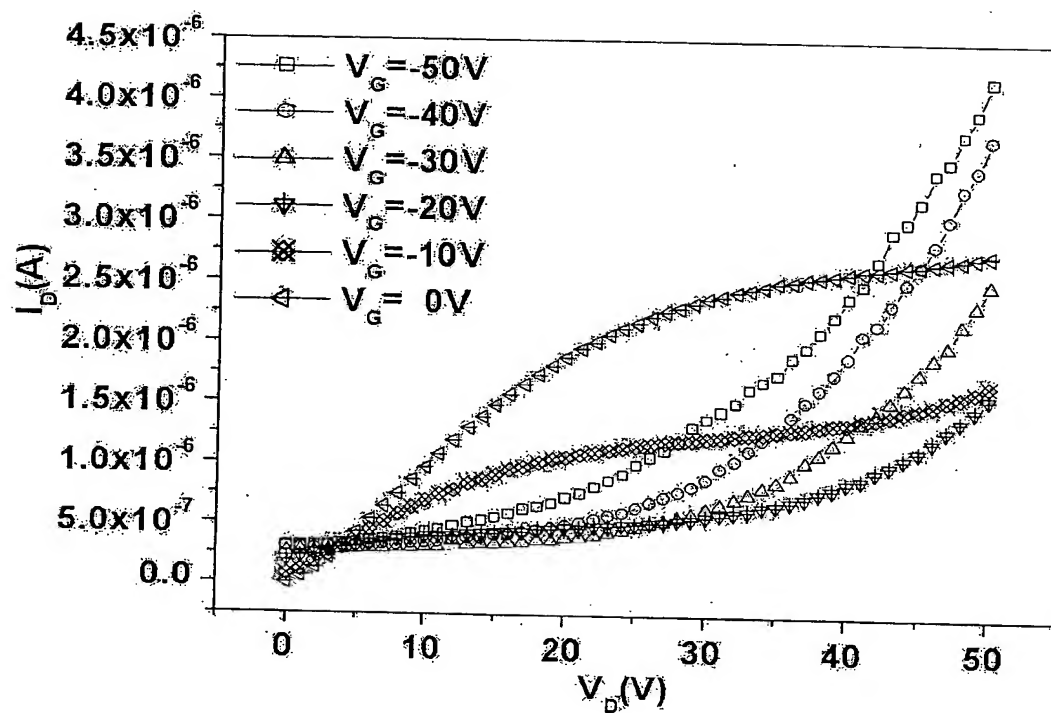


Fig.4

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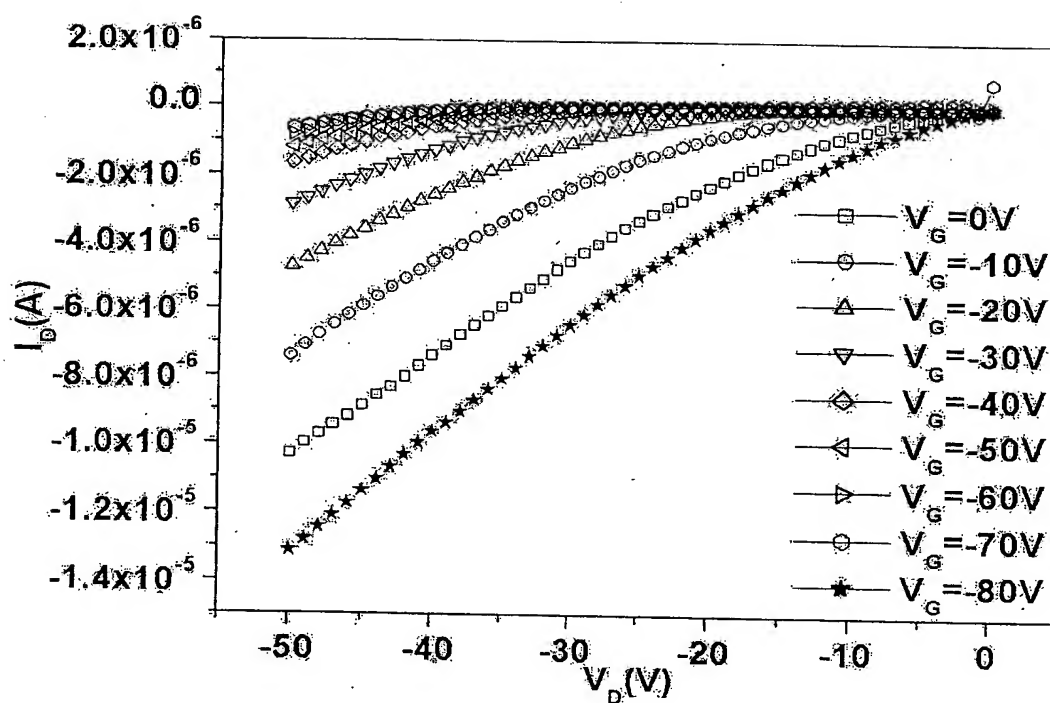


Fig.5

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